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PROCESS FEASIBILITY STUDY IN SUPPORT OF SILICON MATERIAL TASK I

Quarterly Technical Progress Report (XVII), September-November 1979

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QUARTERLY TECHNICAL PROGRESS REPORT (XVII)

Issue Date: December, 1979

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Ku-Yen Li, Keith C. Hansen, and Carl L. Yaws

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ABSTRACT

Analyses were continued for process system properties of chemical materials important in the production of silicon. Primary activities were initiated for physical, transport and thermodynamic property data of silicon. Progress and status including preliminary data collection and analysis results are reported for the primary activities of data collection (90%), data analysis (80%), estimation (70%), and correlation (60%).

Process design results for BCL process-Case A (two deposition reactors and six electrolysis cells) were presented recently. During this reporting period, major chemical engineering efforts were initiated on preliminary process design of the BCL process-Case B (one deposition reactor and two electrolysis cells). Chemical engineering design results are reported for Case B including raw materials, utilities, major process equipment and production labor requirements for a silicon plant of 1,000 MT/yr capacity.

For economic analysis, major efforts centered on cost sensitivity analysis for the BCL process-Case A for producing silicon. Cost sensitivity results are presented for the influence of primary cost parameters. For both 1975 and 1980 time periods, the results indicate that the cost parameter influence on product cost is: plant investment (most), raw materials (intermediate), utilities (intermediate) and labor (least). For profitability, the results indicate a sales price of 14 \$/kg (1980 dollars), at a 7.5% DCF rate of return on investment after taxes. These results suggest good potential of the BCL process for meeting the LSA cost goal of 14\$ per kg (1980 dollars).

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I. PROCESS SYSTEM PROPERTIES ANALYSES (TASK 1)

Analyses were continued for process system properties of chemical materials important in the production of silicon. Primary activities were initiated for physical, thermodynamic, and transport property data of silicon.

The progress for the primary activities and status including preliminary data collection and data analysis results are summarized below:

		Prior	Current
1.	Prel. Data Collection	0%	90%
2.	Data Analysis	· 0%	80%
3.	Estimation Methods	0%	70%
4.	Exp. Corr. Activities	0%	60%
5.	Property Values	0%	55%

The property data coverage for silicon will include critical constants, vapor pressure, heat of vaporization, heat capacity, density, surface tension, viscosity and thermal conductivity. Additional progress including preliminary data collection and data analysis results will be presented in the next report.

II. CHEMICAL ENGINEERING ANALYSIS (TASK 2)

.

A. BCL PROCESS - Case B

Major efforts were initiated on the preliminary process design for Case B of BCL process. In Case B, the process contains one deposition reactor and two electolysis cells as compared with two deposition reactors and six electolysis cells for Case A which was recently reported.

The detailed status for Case B is shown in Table IIA-1.0 to present the items that make up the preliminary process design.

The summarized results for the preliminary process design are presented in a tabular format to make it easier to locate times of specific interest. The guide for these tables is given below:

.Base Case Conditions	IIA-1.1
.Reaction Chemistry	IIA-1.2
.Raw Material RequirementsTable	IIA-1.3
.Utility RequirementsTable	IIA-1.4
.Major Process EquipmentTable	IIA-1.5
.Production Labor RequirementsTable	IIA-1.6

These results were forwarded for preliminary economic analysis.

TABLE IIA-1,0 CHEMICAL ENGINEERING ANALYSES: PRELIMINARY PROCESS DESIGN ACTIVITIES FOR BCL Process (Case B)

	Prel. Process Design Activity	Status	Prel. Process Design Activity Status
1	 Plant Size Product Specifics Additional Conditions 	•	7. Equipment Design Calculations 1. Storage Vessels 2. Unit Operations Equipment 3. Process Data (P, T, rate, etc.) 4. Additional
2	Define Reaction Chemistryl. Reactants, Products2. Equilibrium	•	8. List of Major Process Equipment 1. Size 2. Type
	Process Flow Diagram1. Flow Sequence, Unit Operations2. Process Conditions (T, P, etc.)	• •	3. Materials of Construction • 8a. Major Technical Factors •
ω	 Environmental Company Interaction (Technology Exchange) 	•	(Potential Problem Areas) 1. Materials Compatibility 2. Process Conditions Limitations 3. Additional
4			
2065	 Raw Materials Products By-Products 		9. Production Labor Requirements 1. Process Technology 2. Production Volume
5	Energy Balance Calculations 1. Heating 2. Cooling 3. Additional	• • •	10. Forward for Economic Analysis ●
6	Property Data 1. Physical 2. Thermodynamic 3. Additional	• • •	O Plan ⊕ In Progress ● Complete

TABLE IIA-1.1 BASE CASE CONDITIONS FOR BCL PROCESS (Case B)

- 1. Plant Size
 - -silicon produced from silicon tetrachloride (TET)
 - -1000 metric tons/yr of silicon
 - -solar cell grade silicon
 - -solid phase product form (granules)
- 2. Light End Distillation
 - -purification of TET by distillation
 - -remove 4% chlorosilanes as the light end
 - -80°C, 10 psig
- Heavy End Distillation
 - -purification of TET by distillation
 - -remove 4% impurities as the heavy end
 - -92% over-all yield of TET from both distillations
 - -80°C, 10 psig
- 4. TET Vaporizer
 - -to supply TET vapor for deposition reactor
 - -by power input (resistance heater)
 - -hold at constant level and constant pressure
 - -164°F
- 5. Deposition Reactor
 - -reduce TET by zinc to produce silicon
 - -deposit on pure silicon seed
 - -fluid bed
 - -927°C (1700°F, 1 atm)
 - -63% conversion of TET to silicon
- 6. Reactor Condenser
 - -to condense gases from reactor (ZnCl₂, unreacted Zn and SiCl₄ gases) partial condensation
 - -using therminol 66 as the coolant
 - -927°C inlet temperature and 350°C outlet temperature
- 7. Reactor ZnCl₂ Stripper
 - -work as partial condenser
 - -to condense $\operatorname{ZnCl}_2\operatorname{gas}$ from SiCl_4 gas -
 - -operating at the temperature right above ZnCl₂ melting point (318°C), 350°C
 - -using therminol 66 as the coolant
- 8. Cell ZnCl₂ Stripper
 - -operates as partial condenser
 - -to condense ZnCl_2 gas from Cl_2 and SiCl_4 gases
 - -operating at the temperature right above ZnCl, melting point (318°C), 350°C
 - -using therminol 66 as the heat exchange medium

- 9. Reactor SiCl₄ Condenser
 - -condense SiCl4 gas for recycle
 - -antifreeze as the coolant
 - -350°C inlet temperature, 20°F outlet temperature.
- 10. Electrolysis
 - -electrolytic recovery of Zn from ZnCl2
 - -Cl₂ gas is by product
 - -95% Zn recovery
 - -500°C, approx. 1 atm
- 11. Zinc Vaporizer
 - -to vaporize Zinc
 - -by induction heating
 - -927°C, approx. 1 atm.
- 12. Wastes Treatment
 - -to scrub and neutralize SiCl_4 and chlorosilane gases
 - -caustic solution used to neutralize
- 13. Operating Ratio
 - -approximately 80% utilization (on stream time)
 - -approximately 7,000 hr/yr production
- 14. Storage Considerations
 - -feed material (two week supply)
 - -product (two shifts storage)
 - -process (several hours)

TABLE IIA-1.2 REACTION CHEMISTRY FOR BCL PROCESS (Case B)

1. Silicon Deposition

 $2Zn + SiCl_4 \rightarrow SiV + 2ZnCl_2$

2. Electrolysis

 $ZnCl_2$ electroly. $Zn(1) + Cl_2$ (g)

3. Waste Treatment

$$\operatorname{SiCl}_4 + 2\operatorname{H}_2\operatorname{O} \stackrel{\operatorname{aq}}{\to} \operatorname{SiO}_2 + 4\operatorname{HCl}(\operatorname{aq})$$

$$NaOH(aq) + HCl(aq) \rightarrow NaCl(aq) + H_2O$$

or

 $Ca(OH)_2(aq) + 2HC1(aq) \rightarrow CaCl_2(aq) + 2H_2O$

3a. Waste Treatment (50 MT/yr unit)

 $Cl_2(g) + 2NaOH(aq) \rightarrow NaOCl(aq) + NaCl(aq) + H_2O$

Table IIA-1.3

Raw Material Requirements for BCL Process (Case B)

	Raw Material	Requirements 1b/KG of Silicon
1.	Silicon Tetrachloride, SiCl4	15.33
2.	Zinc, Zn	0.54
3.	Caustic (50%), NaOH(aq)	3.75
or		
	Lime (99%), $Ca(OH)_2$	1.75
4.	Argon	3.1 SCF*
5.	Nitrogen	7.6 SCF*
6.	Chlorine, Cl ₂ (by-product)	11.12

^{*}Estimate from BCL

TABLE IIA-1.4 UTILITY REQUIREMENTS FOR BCL PROCESS (Case B)

Utility/Function Requirements/Kg of Silicon Product 1. Electricity 29,40 Kw-hr Low Voltage D.C. for Electro-(20.51)lysis Zinc Vaporizer Induction Heated (4.37)3. Preheat Section of Deposition (1.12)Unit Induction Heated 4. Electrolysis Feed Tank Heater (0.24)5. Molten Zinc Storage Heater (0.10)SiCl₄ Vaporizer (0.53)rumps, Blowers 7. (2.53)Steam (50 PSIA) 9.67 pounds 1. #1 Purification Column Calandria (4.59)#2 Purification Column Calandria (4.30)3. Caustic Storage Heating (0.29)#1 Purification Column Preheater (0.49) 3. Cooling Water 34.49 Gallons #1 Purification Column Condenser (16.94)#2 Purification Column Condenser (15.88)3. Purified Tet Cooler (1.67)4. Process Water 10.48 Gallons 1. Diluent for Waste Treatment (10.48)5. Refrigeration 2.38 MBtu Reactor SiCl₄ Condenser (H-11) (1.28)

(1.10)

2. SiCl₄ Vent Condenser (H-07)

TABLE IIA-1.5

LIST OF MAJOR PROCESS EQUIPMENT FOR BCL (Case B)

		Equipment	Function	Size/Type	Material of Construction	Capacity Ratio to 1000 MT/yr
	PROC	CESS TOWER AND INTERNA	ALS			
	1.	D-01 Light End Distillation Column	To purify SiCl ₄	8" dia. x 21', packed 13.5'	Column, CS/packing, SS	20
	2.	D-02 Heavy End Distillation Column	To purify SiCl ₄	8" dia. x 21', packed 13.5'	Column, CS/packing, SS	20
	3.	A-01 Primary SiCl ₄ Vent Scrubber	To scrub SiCl ₄ vent gas	3' dia. x 4'4" T/T, 225 gal/flat bottom	FRP	. 1
9	4.	A-02 Final SiCl ₄ Vent Scrubber	To scrub SiCl ₄ vent gas	7'6" dia. x 17'4" T/T/ 4 pp trays, Teflon dimister	FRP	1
	HEA'	I EXCHANGER				
2065	5.	H-01 L.E. Column Feed Heater	To preheat feed to D-01	2' dia. x 5', 15,013 Btu/hr / external heater	CS	20
	6 .	H-02 L.E. Column Reboiler	Reboiler of D-01	2' dia. x 3', 51,522 Btu/hr / external heater	CS .	20
	7.	H-03 L.E. Column Condenser	Total condenser of D-01	47,430 Btu/hr/shell-tube H.E.	CS	20
	8.	H-04 H.E. Column Feed Heater	To preheat feed to D-02	2' dia. x 5', 14,331 Btu/hr/external heater	CS	20

	9.	H-05 H.E. Column Reboiler	Reboiler of D-02	2' dia. x 3', 56,641 Btu/hr/external heater	CS	20
	10.	H-06 H.E. Column Condenser	Total condenser of D-02	52,292 Btu/hr/shell-tube H.E.	CS	20
	11.	H-07 SiCl ₄ Vent Condenser	Condense SiCl ₄ from vent gas	38 ft ² , 18,000 Btu/ hr/shell-tube H.E.	ÇS .	20
	12.	H-08 SiCl ₄ Vaporizer	To provide SiCl ₄ vapor to reactor	2.75' dia. x 3' T/T, 13,648 Btu/hr/ resistance heater	CS	40
	13.	H-09 Reactor Condenser	To condense by products from reactor	14" dia. x 6.4', 126,237.2 Btu/hr	Graphite W/SS shell	40
10	14.	H-10 Reactor ZnCl ₂ Stripper	To condense ZnCl ₂ gas	12 ft ² , 2,652 Btu/hr/ shell-tube H.E., finned U-tube	316 SS	20
	15.	H-11 SiCl ₄ Condenser	To condense SiCl ₄ gas for recycle	6,401 Btu/hr (x 4.62 = 29.573 Btu/hr)	316 SS	20
2065	16.	H-12 Cell ZnCl ₂ Stripper	To condense ZnCl ₂ vapor	9,841.4 Btu/hr/shell- tube, H.E. (x 0.32)	Inconel 600	20
	17.	H-13 Therminol Cooler (cold circuit	To cool Therminol) 66	68 ft ² , 11,000 Btu/hr/ shell-tube H.E., 500 psia	CS	20
	18.	H-14 Therminol Cooler (hot circuit)	To cool Therminol	262 ft ² , 120,000 Btu/hr/ shell-tube H.E., 500 psia		20
	19.	H-15 Start-up Heater	Therminol start- up heater	98,950 Btu/hr/U-tube 15', resistance heater	CS'	. 20
	20.	H-16 Silicon Product Cooler (two)	To cool the Si product from reacto	5,735 Btu/hr r	SiC	40

	20a.	H-17 Chlorination Cooler	,	20,000 Btu/hr, Area 200 ft ²	SS	1
	20b.	H-18 Cell Gas Cooler		1.08 x 10 ⁵ Btu/hr, Area 1805 ft ²	cs	1
	PROCI	ESS AND STORAGE VESSE	<u>LS</u>			
	21.	T-01 SiCl ₄ Storage Tank	Storage/feed to purification	7' dia. x 16' T/T/ 4,600 gal	CS	20
	22.	T-02 SiCl ₄ Emergency Storage Tank	Storage/feed to purification	7' dia. x 16' T/T/ 4,600 gal	CS	20
	23.	T-03 L.E. Column Reflux Drum	To hold distillate for reflux	12" dia. x 4'/23 gal	CS	20
11	24.	T-04 Surge Tank	Surge Tank for D-01 bottom	3' dia. x 4'/200 gal	CS	20
	25.	T-05 Sump Tank	Sump for purification unit	3' dia. x 4'/200 gal	CS	20
2065	26.	T-06 H.E. Column Reflux Drum	To hold distillate for reflux	12" dia. x 4'/23 gal	CS .	20
	27.	T-07 Pure SiCl ₄ Storage Tank	Storage/feed to SiCl ₄ Vaporizer	6' dia. x 10' T/T/ 1900 gal	CS	20
	28.	T-08 Electrolysis Feed Tank	Storage/feed ZnCl ₂ to electrolysis cel		Graphite/304 SS	20
	29.	T-09 Molten Zinc Storage Tank	Storage/feed to Zinc vaporizer	W/heater 68,242 Btu/hr	Graphite/304 SS	20
	30.	T-10 Therminol Head Tank	Storage Therminol	1.5' dia. x 3.75' T/T/ 49.6 gal	CS	20

	31.	T-11 Therminol Drain Down Tank	To store drained Therminol	2.75' dia. x 3' T/T/ 133 gal	CS	20
	32.	T-12 Chlorine Sup- ply Tank	To supply chlorine gas	l 1/2' dia. x 3'/ 37.62 gal	CS	20
	33.	T-13 Lime Storage Tank	Storage Lime	12' dia. x 14'6" T/T/ 12,000 gal	FRP	1
	PUMP	S WITH DRIVERS			• •	
	34.	P-01 Purification Feed Pump	To feed SiCl ₄ to storage tank	30 gpm, 31' head/ centrifugal, 1 1/2 hp	CS	20
	35.	P-02 L.E. Column Feed Pump	To supply SiCl ₄ to preheater	28.9 gph, $\Delta p = 72 \text{ psia/}$ 0.5 hp.	CS	20
12	36.	P-03 L.E. Column Relux Pump	D-01 Reflux	51.7 gph, $\Delta p = 23 \text{ psia/} 0.5 \text{ hp.}$	CS	20
	37.	P-04 Surge Tank	To supply SiCl ₄ to H.E. Column	29.4 gph, $\Delta p = 53 \text{ psia/} 0.5 \text{ hp.}$	CS	20
ડ	38.	P-05 Sump Pump	To pump Sicl ₄ to emergency tank	30 gpm, 31' head/centrifugal, 1 1/2 hp.	CS	20
) 6 7	39.	P-06 L.E. Column Bottom Pump	To pump SiCl ₄ to surge tank	29.4 gph, $\Delta p = 53$ psia/ 0.5 hp.	CS	20
	40.	P-07 H.E. Column Relux Pump	D-02 Reflux	57.1 gph, Δp = 25 psia/ 0.5 hp.	cs	20
	41.	P-08 H.E. Column Bottom Pump	To pump bottom solution to waste treatment	1.3 gph, $\Delta p = 25 \text{ psia/}$ 0.5 hp.	CS	20
	42.	P-09 SiCl ₄ Vaporizer Feed Pump	To feed SiCl ₄ to Vaporizer	15 gph, 31' head/ 1/2 hp	CS	20
		_		·		

	43.	P-10 Reactor Con- denser Circulating Pump	To circulate con- densates	2.4 gpm, 30' head/1/2 hp	Graphite		40
	44.	P-11 Cold Circuit Pump (two)	Cold Therminol circulation	20 gpm, 85' head/centri-fugal, 2 hp.	CS		20
	45.	P-12 Hot Circuit Pump	Hot Therminol circulation	62 gpm, 85° head/centri-fuqal, 4 hp.	CS	,	20
	46.	P-13 Primary Scrubber Recircula- tion Pump	Recirculation for Scrubber A-01	20 gpm, 125' head/centrigugal, 2.5 hp.	Duriron		1
	47.	P-14 Primary Scrubber Lower-loop Recirculating Pump	Circulate solution for Lower-loop of Scrubber A-02	100 gpm, 103' head/ centrifugal, 7 1/2 hp.	Duriron	·	1
13	48.	P-15 Primary Scrubber Upper-loop Recirculating Pump	Circulate solution for upper-loop of Scrubber A-02	100 gpm, 13' head/centrifugal, 2 hp.	Duriron		1
	49.	P-16 Make up Lime Metering Pump	Lime make up	0.9 gpm, 25' head/ centrifugal, 1/2 hp.	CS .		1
2065	FILT	ERS					
	50.	F-01 L.E. Column Feed Filter	Remove solids	29 gph, Δp = 5 psia/ 140 micron	cs		20
	51.	F-02 L.E. Column Reflux Filter	Remove solids	30 gph, $\Delta p = 5 psia/140 micron$	CS		20
	52.	F-03 H. E. Column Feed Filter	Remove solids	52 gph, $\Delta p = 5 \text{ psia/}$ 140 micron	CS		20
	53.	F-04 H.E. Column Relfux Filter	Remove solids	31 gph, $\Delta p = 5 psia/140 micron$	CS		20

	54.	F-05 Therminol Cooler Blower Filter	To filter the solid from air	s		20
	SPEC	IALIZED EQUIPMENTS				
	55.	R-01 Fluidized Bed Reactor (two)	To reduce SiCl ₄ to Si by Zn	1830.2 Btu/hr, 6.5" dia.	Graphite Lined / SS	40
	56.	FN-01 Furnace (two)	To preheat SiCl ₄ gas	272,966 Btu/hr		40
	57.	B-01 Seed Addition Hopper (two)	To feed Si seed to the reactor		310 SS	40
L	58.	B-02 Si Product Hopper (four)	To hold Si product	6 gal	310 SS	20
14	59.	B-03 Zinc Hopper	To hold make up Zinc	40 gal	cs	20
	60.	C-01 Therminol Cooler Blower	Therminol system air cooler blower	500 acfm fan/electric, 1 1/2 hp., 12-1/2" wheel	cs	20
2065	61.	C-02 Scrubber Vent	Suck SiCl ₄ gas for A-01 & A-02	10,000 acfm/electric, 50 hp. 31-1/2" wheel	FRP	1
	62.	E-01 Eductor (two)	SiCl ₄ scrubbing (Scrubber D-05)	20 gpm, Δp = 47.4 psia/ Hydraulic ejector, 1-1/2" NPT	P.V.C.	1
•	63.	EC-01 Electrolysis Cell (six)	To recover Zn from ZnCl ₂	5,000 ~6,000 amp cells	Graphite/SS	60
	64.	PW-01 Power Supply	To supply power to electrolysis cell	545,933 Btu/hr.		20
	65.	VP-01 Zinc Vaporizer (two)	To provide zinc vapor to reactor	104,128.8 Btu/hr 13.5" dia. x 32"	Quartz	· 4 0

NOTE:

- 1. For the 1000 MT/yr plant, items 3, 4, 33, 46, 47, 48, 49, 61, and 62 are used for waste treatment of distillation wastes (light, heavy) and vent gases.
- 2. In the 50 MT/yr facility, these items are used for hypochlorite maufacture which is not present in the 1000 MT/yr plant.
- 3. For H-11, the operation conditions were changed from 171°F 32°F to 662°F 20°F.
- 4. For H-12, the operations conditions have been changed from $\Delta T = 855$ °F to 270°F.

TABLE IIA-1.6

PRODUCTION LABOR REQUIREMENTS FOR BCL PROCESS (Case B)

			Labor	•
	Section		man-hr/KG Si	(oper/shift)
1.	Purification	(I)	0.01402	(2)
2.	Deposition	(II)	0.01402	(2)
3.	Electrolysis	(III)	0.02103	(3)
4.	Waste Treatment	(IV)	0.00701	(1)
5.	Product Handling	(V)	0.00701	(1)
		TOTAL	0.06309	(9)

Note

Manpower estimate for production labor requirements based on:

- Dividing plant into sections-type of unit operation-mark off working area
- 2. Specify work duties required in each section
- 3. Estimate operators required to perform work duties in each section
 - -type of unit operation
 - -size of working area
 - -degree of automation (batch, semi-continuous, continuous, etc.)

B. OTHER PROCESSES

Other processes (such as SRI process, UCC silane process, Hemlock Semiconductor process, etc.) under consideration for solar cell grade silicon production are being monitored with respect to data relative to chemical engineering analysis.

III. ECONOMIC ANALYSIS (TASK 3)

During this reporting period, economic analysis was continued for the BCL process - Case A for producing silicon. Case A is based on two deposition reactors (approx. 2 ft. dia.) and six electrolysis cells. Major efforts centered on cost sensitivity analysis of the process including the influence of raw materials, labor, utilities and capital investment.

The status and progress achieved since the last reporting period are summarized below for the subitems making up the cost sensitivity analysis:

		Prior	Current
1.	Base Case Conditions	40%	100%
2.	Return on Orig. Invest.	10%	100%
3.	Discounted Cash Flow Rate of Return	40%	100%
4.	Plant Invest. Cost Var.	40%	100%
5.	Raw Material Cost Var.	40%	100%
6.	Utilities Cost Var.	40%	100%
7.	Labor Cost Var.	40%	100%
8.	Effect of Inflation	40%	100%
9.	Cost and Profitability Analysis		
	Summary	40%	100%

A detailed status sheet showing that these activities are completed is presented in Table III-1.0.

The preliminary cost sensitivity analysis is being performed to determine the influence of cost parameters on the economics of producing silicon by this new technology. The cost sensitivity results for the 1975 time period are given in Figure III-1.1 in which product cost (\$/kg Si) is plotted versus variation (-100% to 0% to +100%) of the primary cost parameters (plant investment, raw materials, labor and utilities). The 0% variation represents the base case. The -100% variation corresponds to the case of no costs for the parameters; and the +100% represents the case for the doubling of cost for each parameter. The plot illustrates that product cost is influenced most by plant investment and least by utilities.

The cost sensitivity results for the 1980 time period are presented in Figure III-1.2 for the primary cost parameters. The results indicate that the cost parameter influence on product cost is: plant investment (most), raw materials (intermediate), utilites (intermediate) and labor (least).

The product cost represents all cost associated with producing one kilogram of silicon. On top of these costs a producing company will include some profit. The sales price of the product silicon will actually be the sum of the product cost and a profit for the company. The profit is usually measured in terms of rate of return on the capital investment that the company spent in going into the polysilcion business. Two profitability methods which are commonly used are the retun on original investment (%ROI) and discounted cash flow rate of return (%DCF).

The cost and profitability analysis summary for this process are presented in Table III-1.3 for both 1975 and 1980 time periods. The sales price of polysilicon at various rates or return for both profitability mehtods (%ROI and %DCF) is shown in the lower half of the table. The results indicate a sales price of 10 \$/kg of silicon (1975 dollars), or 14 \$/kg (1980 dollars), at a 7.5 %DCF rate of return after taxes for the process. This means that this process has good potential to meet the LSA cost goal for 10% per kg (1975 dollars) or 14% per kg (1980 dollars).

The effect of inflation (higher costs for raw material, utilities, labor, etc.) is shown in Figure III-1.4. For the figure, product cost is plotted against time at various inflation levels (0%, 5%, 7%, and 10% inflation) for the 1975-1990 time period.

TABLE III-1.0

COST SENSITIVITY ANALYSIS: PRELIMINARY COST SENSITIVITY ACTIVITIES FOR BCL PROCESS (Case A)

	Prel. Sensitivity Activity	Status	Prel. Sensitivity Analysis	Status
1.	Specify Base Case Conditions 1. Process 2. Plant Size 3. Product 4. Cost Data	• 6 • • • • • • • • • • • • • • • • • •	Utilities Cost Variation 1. Steam 2. Electricity 3. Cooling Water 4. Process Water	•
2.	Return on Original Investment 1. Capital Investment 2. Taxes 3. % ROI	•	 Other Labor Cost Variation Production Labor Labor Fate Staffing Estimate 	•
3. D	Discounted Cash Flow Rate of Return 1. Capital Investment 2. Taxes 3. % DCF	• • 8	8. Effect of Inflation 1. Rate 2. Future	•
4. 2065	Plant Investment Cost Variation 1. Major Process Equipment 2. Installation, Picint 3. Instrumentation, Buildings 4. Offsites 5. Indirects, Engineering 6. Fixed, Working Capital 7. Other	• 9 • • • • • • • • • • • • • • • • • •	 Cost and Profitability Analysis Summary Plant Investment Product Cost Sales Frice (Profit) 	•
5.	Raw Material Cost Variation 1. Major Raw Materials 2. Waste Treatment 3. By-Product	•	<pre>0 Plan 9 In Progress • Complete</pre>	. •

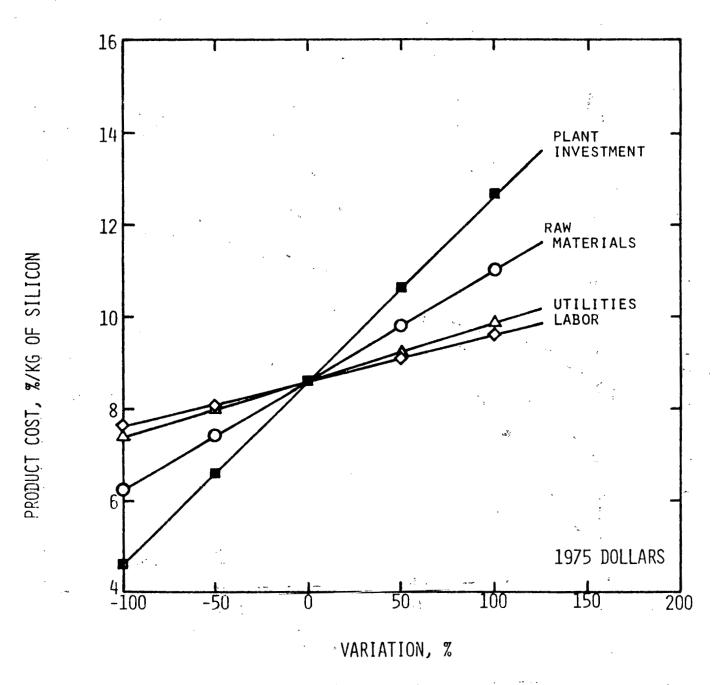


Figure III-1.1 COST SENSITIVITY ANALYSIS OF BCL PROCESS

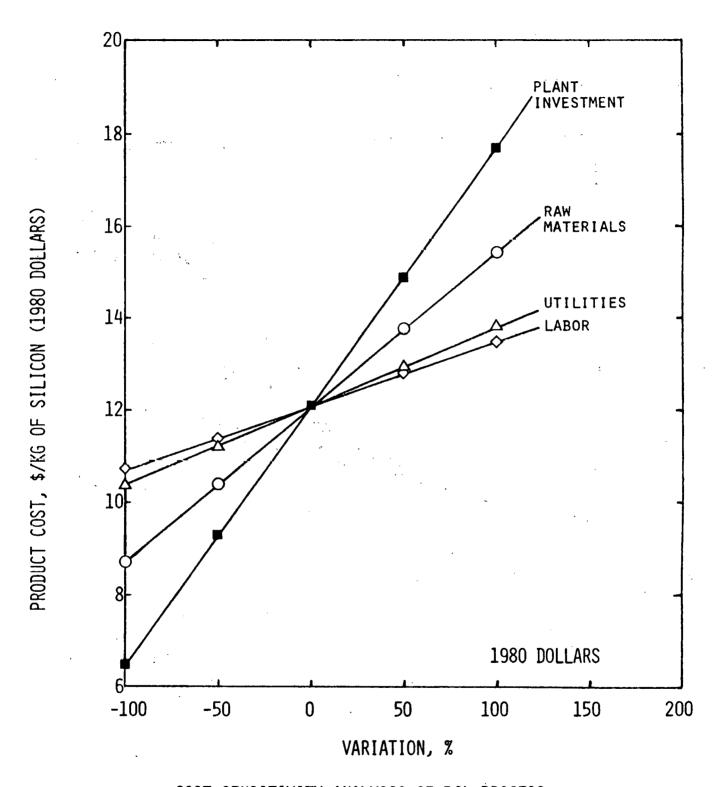


Figure III-1.2 COST SENSITIVITY ANALYSIS OF BCL PROCESS

TABLE III-1.3

COST AND PROFITABILITY ANALYSIS SUMMARY FOR BCL PROCESS

1.	Process	• • • • • • • • • • • • • • •	.BCL Process						
2.	Plant Size	• • • • • • • • • • • • • • •	.1,000 Metric Tons/year						
3.	Plant Product	• • • • • • • • • • • • • • •	Silicon						
4.	Product Form	• • • • • • • • • • • • • • •	.Silicon Granules						
5.	Plant Investment	• • • • • • • • • • • • • • • •	.\$14,340,000/\$20,070,000						
		(19	975 dollars) (1980 dollars)						
	Fixed Capita	al	\$12.47 Mega \$17.45 Mega						
	Working Cap	ital	1.87 Mega 2.62 Mega						
	(15%)	TOTAL	\$14.34 Mega \$20.07 Mega 975 dollars) (1980 dollars)						
		•	,						
6.	Product Cost	• • • • • • • • • • • • • • • •	.8.63 \$/Kg (1975 dollars)						
7.	Tax Rate (Federal)	• • • • • • • • • • • • • •	.46%						
8.	Return on Original Investment,	after taxes (%RC	OI)						
		Sales Price	Sales Price						
		\$/Kg of Silicon	\$/Kg of Silicon						
		(1975 dollars)	_						
	ON ROI		12.08						
	54 ROI		13.94						
	10% ROI		15.80						
	154 ROI		17.65						
	20% ROI		19.51						
	25% ROI	•	21.37						
	30% ROI		23.23						
	40% ROI	. 19.25	26.95						
9.	Discounted Cash Flow Rate of Re	eturn, after taxo	es (%DCF)						
		Sales Price	Sales Price						
		\$/Kg of Silicon							
		(1975 dollars)	· · · · · · ·						
	0% DCF	. 8.63	12.08						
	5% DCF	. 9.48 ~	13.28						
	100 000	10.40	14 60						

Based on 10 year project life and 10 year straight line depreciation.

10.42

11.44

12.52

13.65

14.83

17.27

10% DCF.....

15% DCF.....

20% DCF.....

25% DCF.....

30% DCF.....

40% DCF.....

13.28 14.59

16.01

17.53

19.11

20.76

24.18

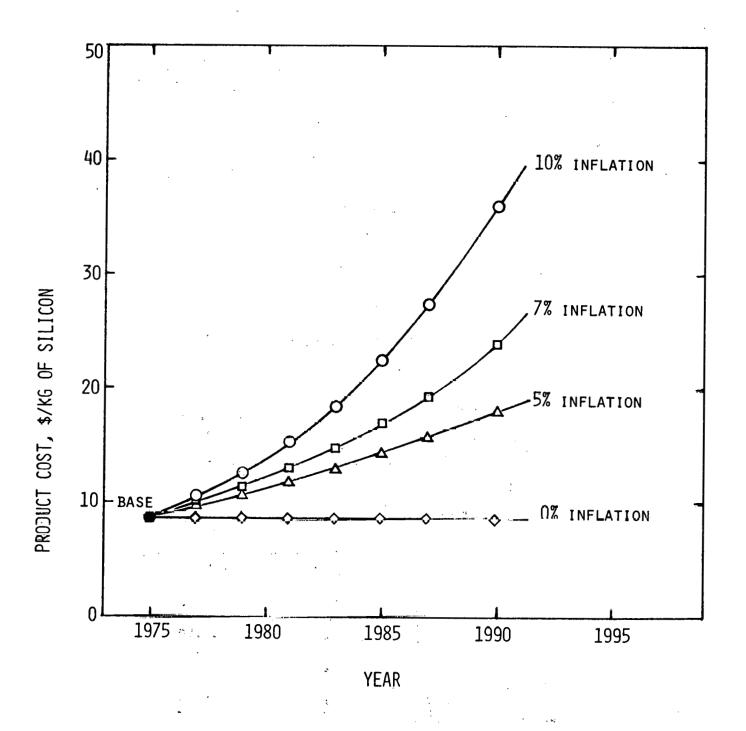


Figure III-1.4 INFLATION EFFECT

IV. SUMMARY - CONCLUSIONS

Based on achievements during this reporting period, the following summary-conclusions are made:

1. Task 1

Process system properties analyses were continued for chemical materials important in the production of silicon. Major activities were initiated for physical, transport and thermodynamic property data for silicon. Status and progress are reported for data collection (90%), data analysis (80%), estimation (70%) and correlation (60%).

2. Task 2

Process design results for BCL process - Case A (two deposition reactors and six electrolysis cells) were presented during the last reporting period. During this reporting period, major chemical engineering efforts were initiated on preliminary process design of the BCL process - Case B (one deposition reactor and two electrolysis cells). Chemical engineering design results are reported for Case B including raw materials, utilities, major process equipment and production labor requirements for a silicon plant of 1,000 MT/yr capacity.

3. Task 3

For economic analysis, major efforts centered on cost sensitivity analysis of the BCL process - Case A for producing silicon. Cost sensitivity results are presented for the influence of primary cost parameters. For both 1975 and 1980 time periods, the results indicate that the cost parameter influence on product cost is: plant investment (most), raw materials (intermediate), utilities (intermediate) and labor (least). For profitability, the results indicate a sales price of 14 \$/kg (1980 dollars), at a 7.5 %DCF rate of return on investment after taxes. These results suggest good potential of the BCL process for meeting the LSA cost goal of 14\$ per kg (1980 dollars).

V. PLANS

Plans for the next reporting period are summarized below:

1. Task l

Continue analysis of process system properties for chemical materials important to the production of silicon.

2. Task 2

Continue chemical engineering analysis of processes under consideration for producing silicon.

3. Task 3

Perform economic analysis of processes as results issue from chemical engineering analysis.

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2.Data Analysis												;				٠.									
3.Estimation Methods																									
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PROCESS FEASIBILITY STUDY IN SUPPORT OF SILICON MATERIAL TASK I

JPL Contract No. 954343